



## JR0205 Series Sensitive gate SCRs

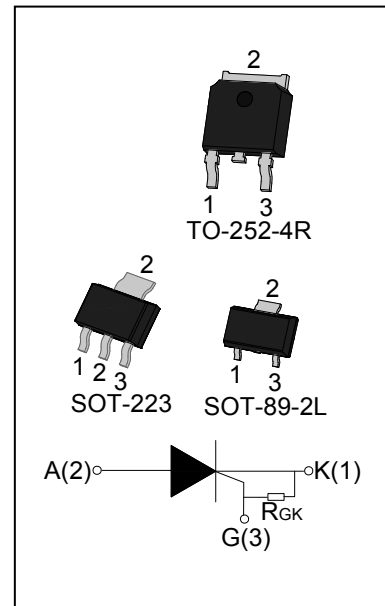
Rev.9.0

### DESCRIPTION:

The JR0205 SCR series with the parallel resistor between Gate and Cathode are especially recommended for use on straight hair, igniter, anion generator, etc. All the packages listed above are RoHS compliant. (2011/65/EU)

### MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	2	A
$I_{GT}$	$\leq 200$	$\mu A$
$V_{TM}$	$\leq 1.5$	V



### ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		$T_{stg}$	-40-150	$^{\circ}C$
Operating junction temperature range		$T_j$	-40-125 <sup>①</sup>	$^{\circ}C$
Repetitive peak off-state voltage		$V_{DRM}$	600	V
Repetitive peak reverse voltage		$V_{RRM}$	600	V
RMS on-state current	TO-252-4R ( $T_c=72^{\circ}C$ )	$I_{T(RMS)}$	2	A
	SOT-223/ SOT-89-2L( $T_c=65^{\circ}C$ )			
Non repetitive surge peak on-state current ( $t_p=10ms$ )		$I_{TSM}$	20	A
$I^2t$ value for fusing ( $t_p=10ms$ )		$I^2t$	2	$A^2s$
Critical rate of rise of on-state current		$di/dt$	50	$A/\mu s$
Peak gate current ( $t_p=20\mu s$ , $T_j=125^{\circ}C$ )		$I_{GM}$	0.2	A
Peak gate power ( $t_p=20\mu s$ , $T_j=125^{\circ}C$ )		$P_{GM}$	0.5	W
Average gate power dissipation( $T_j=125^{\circ}C$ )		$P_{G(AV)}$	0.1	W

**NOTE 1:** When we parallel connect a  $\leq 1K\Omega$  resistor between Gate and Cathode, the  $T_j$  can reach  $125^{\circ}C$ ; if without this resistor, the  $T_j$  only can reach  $110^{\circ}C$ .

ELECTRICAL CHARACTERISTICS ( $T_j=25^{\circ}\text{C}$  unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
$I_{GT}$	$V_D=12\text{V}$ $R_L=33\Omega$	-	40	200	$\mu\text{A}$
$V_{GT}$		-	0.5	0.8	V
$V_{GD}$	$V_D=V_{DRM}$ $T_j=125^{\circ}\text{C}$	0.2	-	-	V
$I_L$	$I_G=1.2 I_{GT}$	-	-	3	mA
$I_H$	$I_T=0.05\text{A}$	-	-	2	mA
dV/dt	$V_D=60\%V_{DRM}$ $T_j=125^{\circ}\text{C}$ $R_{GK}=1\text{K}\Omega$	10	-	-	V/ $\mu\text{s}$

## STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
$V_{TM}$	$I_{TM}=4\text{A}$ $t_p=380\mu\text{s}$	$T_j=25^{\circ}\text{C}$	1.5	V
$I_{DRM}$	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^{\circ}\text{C}$	5	$\mu\text{A}$
$I_{RRM}$		$T_j=125^{\circ}\text{C}$	100	$\mu\text{A}$

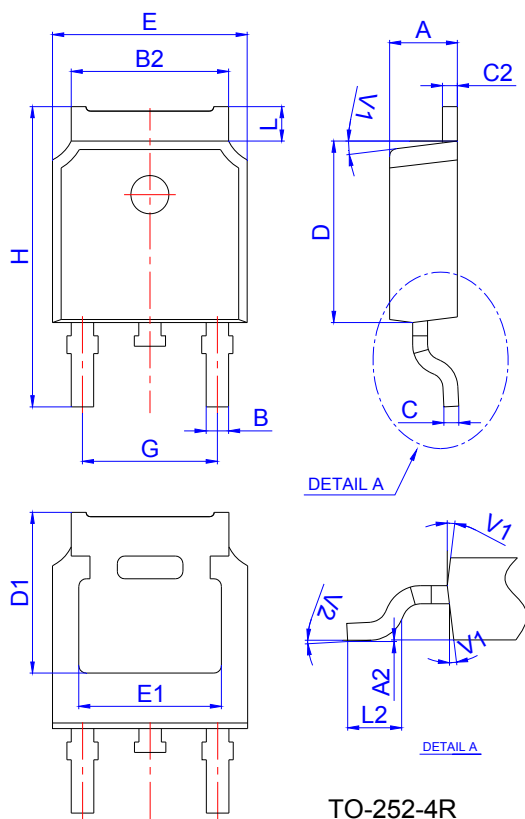
## THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case	TO-252-4R	6.5	$^{\circ}\text{C}/\text{W}$
		SOT-223	20	
		SOT-89-2L	25	
$R_{th(j-a)}$	junction to ambient	TO-252-4R	70	
		SOT-223	60	
		SOT-89-2L	90	

**ORDERING INFORMATION**

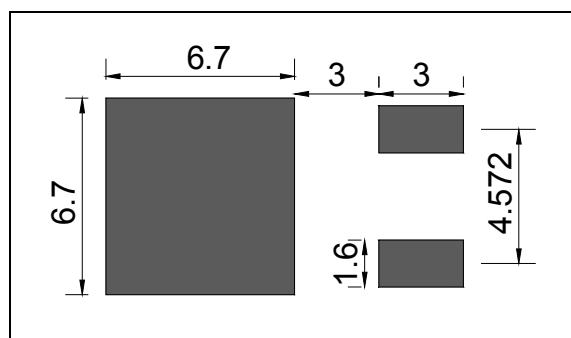
<p>JieJie Microelectronics Co.,Ltd</p> <p>Sensitive gate SCRs</p>	<p><b>J R 02 05 V</b></p>	<p>V:SOT-223 K:TO-252-4R N2:SOT-89-2L KTR:TO-252-4R(Tape&amp;Reel)</p> <p>05:IGT ≤ 200μA</p> <p>IT(RMS):2A</p>
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**PACKAGE MECHANICAL DATA**

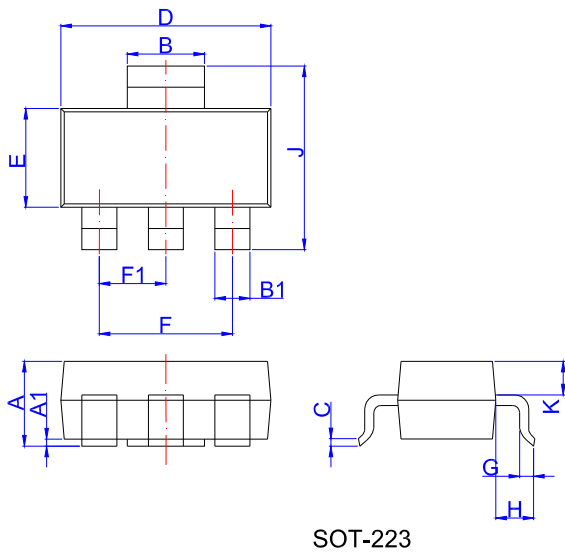


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

**FOOTPRINT-TO-252-4R (dimensions in mm)**

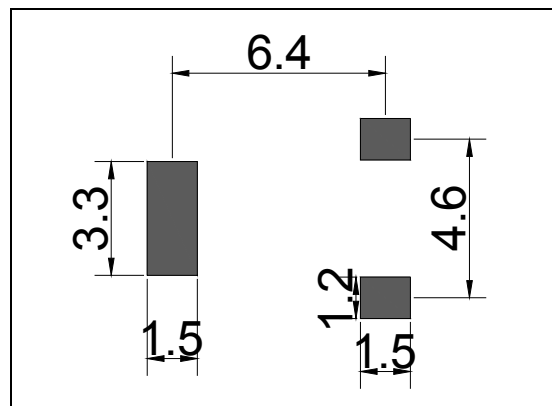


**PACKAGE MECHANICAL DATA**

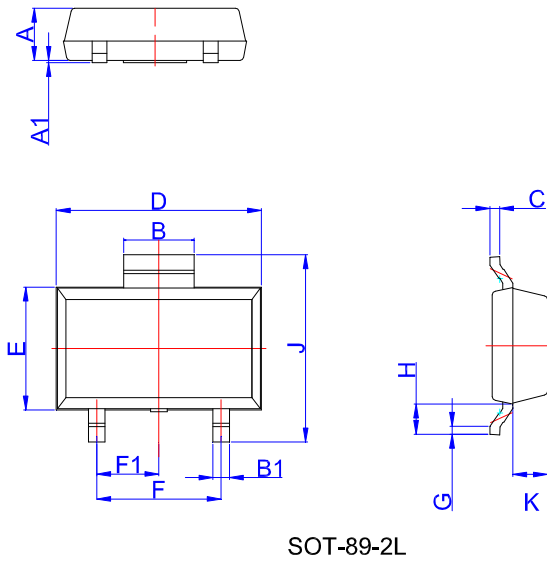


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	1.5	1.6	1.8	0.059	0.063	0.071
A1	0.01	0.06	0.10	0.001	0.002	0.004
B	2.9	3.0	3.1	0.114	0.118	0.122
B1	0.6	0.7	0.8	0.024	0.028	0.031
C	0.22	0.26	0.32	0.009	0.010	0.013
D	6.3	6.5	6.7	0.248	0.256	0.264
E	3.3	3.5	3.7	0.130	0.138	0.146
F		4.6			0.181	
F1		2.3			0.091	
G	0.7	0.9	1.1	0.028	0.035	0.043
H	1.5	1.75	2.0	0.059	0.069	0.079
J	6.7	7.0	7.3	0.264	0.276	0.287
K	0.8	0.9	1.0	0.031	0.035	0.039

**FOOTPRINT-SOT-223-2L (dimensions in mm)**

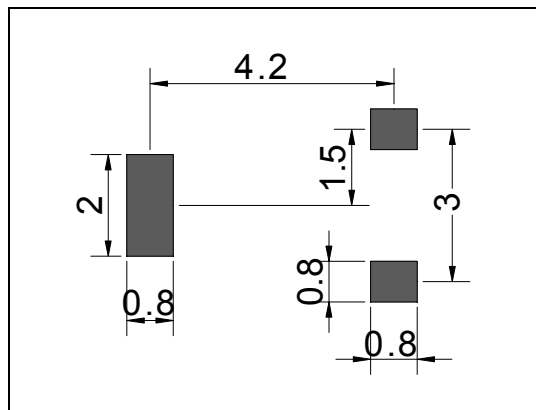


**PACKAGE MECHANICAL DATA**

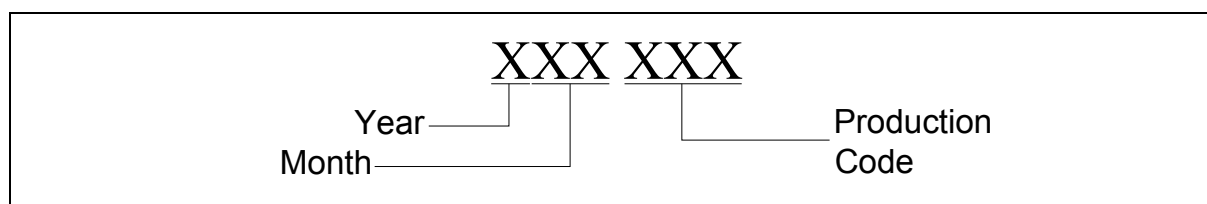
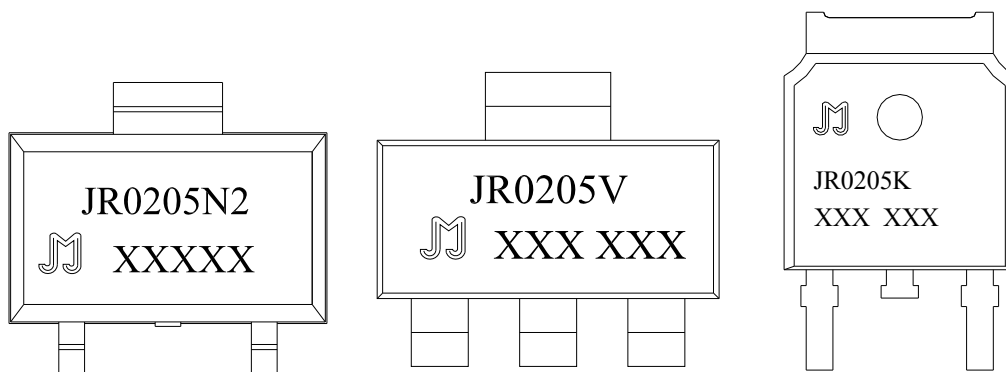


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	1.3	1.4	1.5	0.051	0.055	0.059
A1	0.01	0.06	0.10	0.001	0.002	0.004
B	1.6	1.7	1.8	0.063	0.067	0.071
B1	0.3	0.4	0.5	0.012	0.016	0.020
C	0.22	0.254	0.32	0.009	0.010	0.013
D	4.75	4.95	5.15	0.187	0.195	0.203
E	2.75	2.95	3.15	0.108	0.116	0.124
F		3.0			0.118	
F1		1.5			0.059	
G	0.2	0.3	0.4	0.008	0.012	0.016
H	0.58	0.78	0.98	0.023	0.031	0.039
J	4.3	4.5	4.7	0.169	0.177	0.185
K		0.88			0.035	

**FOOTPRINT-SOT-89-2L (dimensions in mm)**



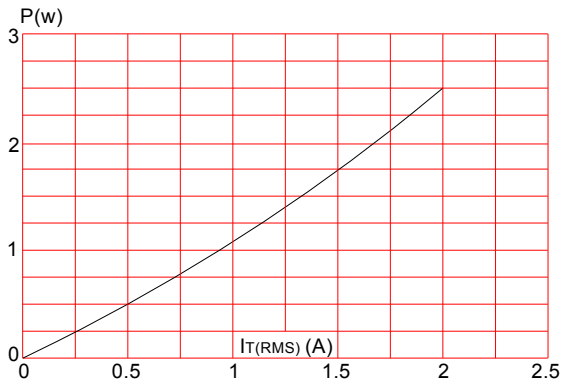
**MARKING**



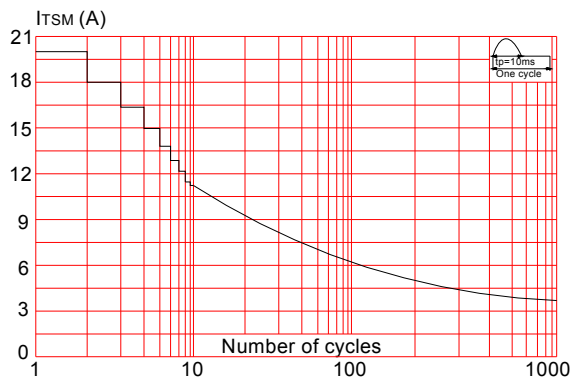
**PACKAGE INFORMATION**

PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-252-4R	TUBE	80	4,000	32,000
PACKAGE	OUTLINE	REEL (PCS)	PER CARTON (PCS)	TAPE & REEL
TO-252-4R	TAPING	2,500	25,000	13 inch
SOT-223	TAPING	4,000	40,000	13 inch
SOT-89-2L	TAPING	4,000	40,000	13 inch

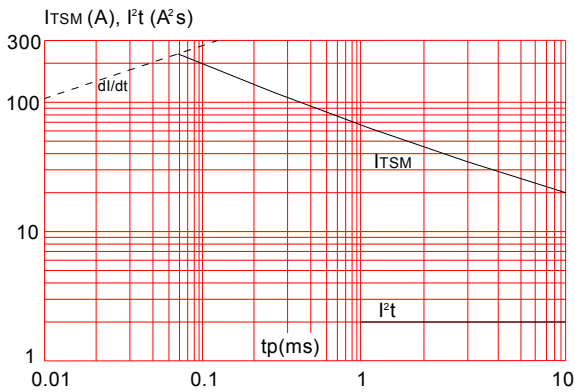
**FIG.1:** Maximum power dissipation versus RMS on-state current



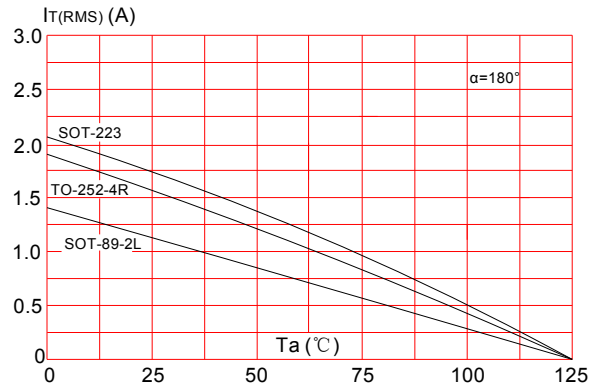
**FIG.3:** Surge peak on-state current versus number of cycles



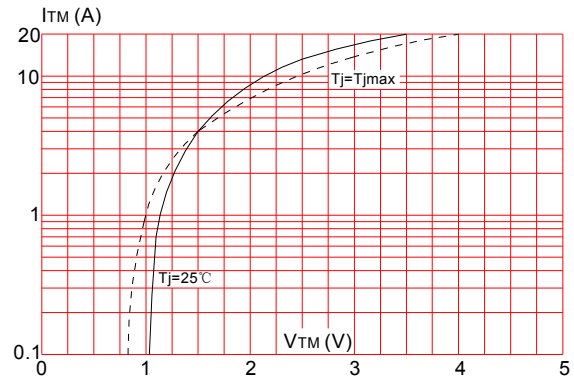
**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 10\text{ms}$ , and corresponding value of  $I^2t$  ( $di/dt < 50\text{A}/\mu\text{s}$ )



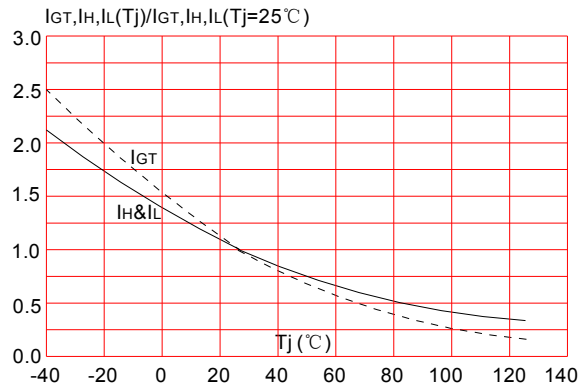
**FIG.2:** RMS on-state current versus ambient temperature (printed circuit board FR4, copper thickness:  $35\mu\text{m}$ ) (full cycle)



**FIG.4:** On-state characteristics (maximum values)

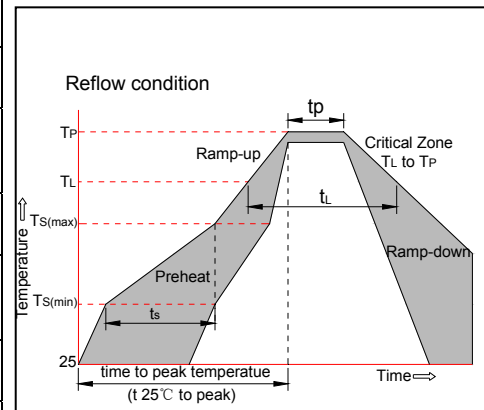


**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature




## SOLDERING PARAMETERS

Reflow Condition		Pb-Free assembly (see figure at right)
Pre Heat	-Temperature Min ( $T_{s(min)}$ )	+150°C
	-Temperature Max( $T_{s(max)}$ )	+200°C
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquidus Temp ( $T_L$ ) to peak)		3°C/sec. Max
$T_{s(max)}$ to $T_L$ - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature( $T_L$ ) (Liquidus)	+217°C
	-Temperature( $t_L$ )	60-150 secs.
Peak Temp ( $T_P$ )		+260(+0/-5)°C
Time within 5°C of actual Peak Temp ( $t_p$ )		20-40secs.
Ramp-down Rate		6°C/sec. Max
Time 25°C to Peak Temp ( $T_P$ )		8 min. Max
Do not exceed		+260°C



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